

## **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The NCEP1520G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

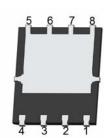
#### **General Features**

- $V_{DS}$  =150V, $I_D$  =20A  $R_{DS(ON)}$ =59m $\Omega$  (typical) @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

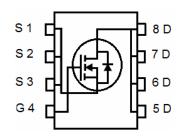
#### **DFN 5X6**





**Top View** 

**Bottom View** 



**Schematic Diagram** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1520G	NCEP1520G	DFN5X6-8L	-	-	-

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	150	V	
Gate-Source Voltage	V <sub>GS</sub>	±20	V	
Drain Current-Continuous	I <sub>D</sub>	20	Α	
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	14	Α	
Pulsed Drain Current	I <sub>DM</sub>	80	Α	
Maximum Power Dissipation	P <sub>D</sub>	68	W	
Derating factor		0.54	W/℃	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	65	mJ	
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}$	

## **Thermal Characteristic**

Thermal Résistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ heta JC}$	1.84	°C/W
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# Electrical Characteristics ( $T_A$ =25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Symbol Condition		Тур	Max	Unit
Off Characteristics				•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•	I.		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.5	3.3	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	-	59	65	mΩ
Gate resistance	$R_G$		-	4.5	-	Ω
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =10A	15	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>	.,	-	600		PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =75 $V$ , $V_{GS}$ =0 $V$ ,	-	74.7		PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	10.8		PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	9.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =75 $V$ , $R$ L=7.5 $\Omega$	-	5.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10 $V$ , $R_{G}$ =3 $\Omega$	-	12.5	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg	)/ 75\/\ 404	-	12	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =75V,I <sub>D</sub> =10A,	-	2.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	1.8	-	nC
Drain-Source Diode Characteristics			•	I.		
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	20	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$	-	29	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	130	-	nC

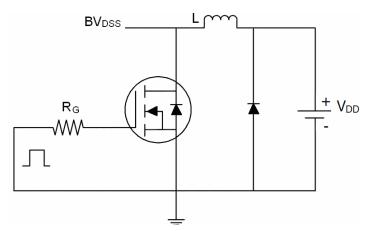
#### Notes:

- ${\it 1. Repetitive Rating: Pulse width \ limited \ by \ maximum \ junction \ temperature.}$
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

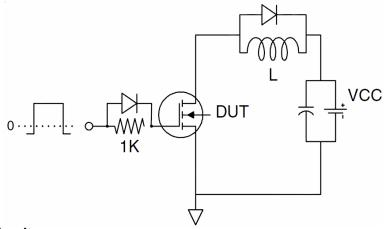


## **Test Circuit**

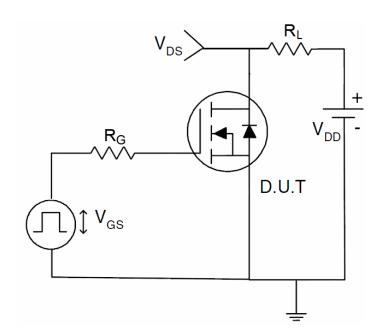
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

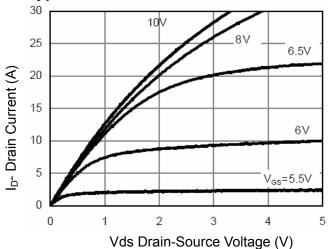


## 3) Switch Time Test Circuit

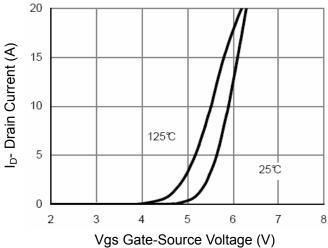




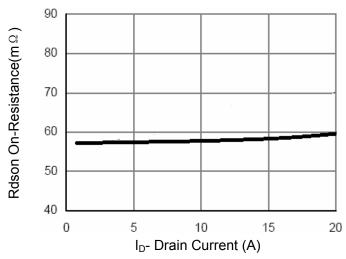
## **Typical Electrical and Thermal Characteristics**



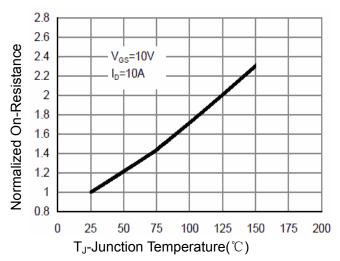
**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 



**Figure 3 Rdson- Drain Current** 



**Figure 4 Rdson-Junction Temperature** 

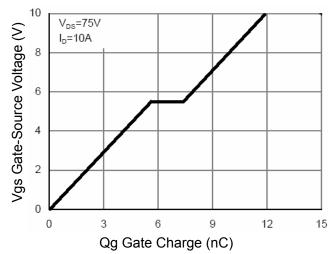


Figure 5 Gate Charge

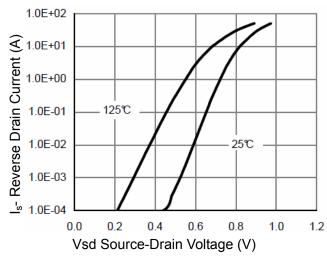
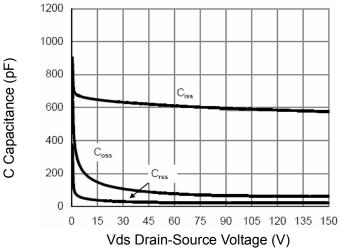


Figure 6 Source- Drain Diode Forward

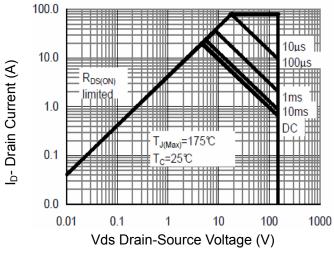


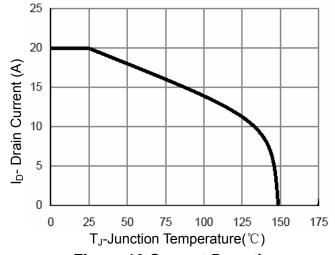


120 100 Power Dissipation (W) 80 60 40 20 0 25 50 75 100 125 0 150 175  $T_J$ -Junction Temperature( $^{\circ}$ C)

Figure 7 Capacitance vs Vds

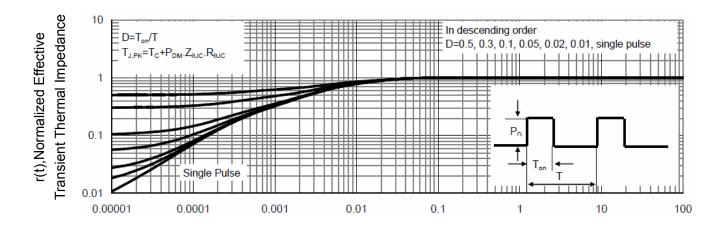
Figure 9 Power De-rating





**Figure 8 Safe Operation Area** 

Figure 10 Current De-rating

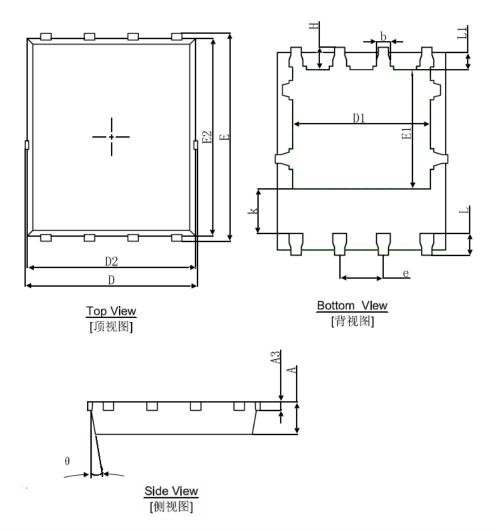


Square Wave Pluse Duration(sec)

**Figure 11 Normalized Maximum Transient Thermal Impedance** 



## **DFN5X6-8L Package Information**



Cumahad	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254	REF.	0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
e	1.270TYP.		0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	

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# NCEP1520G

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